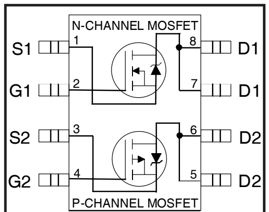
International
IOR Rectifier

PD - 96115

IRF9952QPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dual N and P Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- 150°C Operating Temperature
- Automotive [Q101] Qualified
- Lead-Free



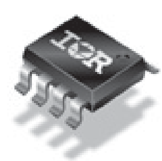
Top View

	N-Ch	P-Ch
V_{DSS}	30V	-30V
$R_{DS(on)}$	0.10Ω	0.25Ω

Description

Specifically designed for Automotive applications, these HEXFET® Power MOSFET's in a Dual SO-8 package utilize the lastest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of these Automotive qualified HEXFET Power MOSFET's are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

The efficient SO-8 package provides enhanced thermal characteristics and dual MOSFET die capability making it ideal in a variety of power applications. This dual, surface mount SO-8 can dramatically reduce board space and is also available in Tape & Reel.



SO-8

		Symbol	Maximum		Units
			N-Channel	P-Channel	
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current⑤	T_A = 25°C	I_D	3.5	-2.3	A
	T_A = 70°C		2.8	-1.8	
Pulsed Drain Current		I_{DM}	16	-10	
Continuous Source Current (Diode Conduction)		I_S	1.7	-1.3	
Maximum Power Dissipation ⑤	T_A = 25°C	P_D	2.0		W
	T_A = 70°C		1.3		
Single Pulse Avalanche Energy		E_{AS}	44	57	mJ
Avalanche Current		I_{AR}	2.0	-1.3	A
Repetitive Avalanche Energy		E_{AR}	0.25		mJ
Peak Diode Recovery dv/dt ②		dv/dt	5.0	-5.0	V/ ns
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to + 150		°C

Thermal Resistance Ratings

Parameter	Symbol	Limit	Units
Maximum Junction-to-Ambient ⑤	$R_{\theta JA}$	62.5	°C/W

07/23/07

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter		Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	N-Ch	30	—	—	V	V_{GS} = 0V, I_D = 250µA
		P-Ch	-30	—	—		V_{GS} = 0V, I_D = -250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	N-Ch	—	0.015	—	V/°C	Reference to 25°C, I_D = 1mA
		P-Ch	—	0.015	—		Reference to 25°C, I_D = -1mA
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	N-Ch	—	0.08	0.10	Ω	V_{GS} = 10V, I_D = 2.2A ④
			—	0.12	0.15		V_{GS} = 4.5V, I_D = 1.0A ④
		P-Ch	—	0.165	0.250		V_{GS} = -10V, I_D = -1.0A ④
			—	0.290	0.400		V_{GS} = -4.5V, I_D = -0.50A ④
$V_{GS(th)}$	Gate Threshold Voltage	N-Ch	1.0	—	—	V	V_{DS} = V_{GS}, I_D = 250µA
		P-Ch	-1.0	—	—		V_{DS} = V_{GS}, I_D = -250µA
g_{fs}	Forward Transconductance	N-Ch	—	12	—	S	V_{DS} = 15V, I_D = 3.5A ④
		P-Ch	—	2.4	—		V_{DS} = -15V, I_D = -2.3A ④
I_{DSS}	Drain-to-Source Leakage Current	N-Ch	—	—	2.0	µA	V_{DS} = 24V, V_{GS} = 0V
		P-Ch	—	—	-2.0		V_{DS} = -24V, V_{GS} = 0V
		N-Ch	—	—	25		V_{DS} = 24V, V_{GS} = 0V, T_J = 125°C
		P-Ch	—	—	-25		V_{DS} = -24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	N-P	—	—	±100	nA	V_{GS} = ±20V
Q_g	Total Gate Charge	N-Ch	—	6.9	14	nC	N-Channel I_D = 1.8A, V_{DS} = 10V, V_{GS} = 10V ④ P-Channel I_D = -2.3A, V_{DS} = -10V, V_{GS} = -10V
		P-Ch	—	6.1	12		
Q_{gs}	Gate-to-Source Charge	N-Ch	—	1.0	2.0		
		P-Ch	—	1.7	3.4		
Q_{gd}	Gate-to-Drain ("Miller") Charge	N-Ch	—	1.8	3.5		
		P-Ch	—	1.1	2.2		
$t_{d(on)}$	Turn-On Delay Time	N-Ch	—	6.2	12	ns	N-Channel V_{DD} = 10V, I_D = 1.0A, R_G = 6.0Ω, R_D = 10Ω ④ P-Channel V_{DD} = -10V, I_D = -1.0A, R_G = 6.0Ω, R_D = 10Ω
		P-Ch	—	9.7	19		
t_r	Rise Time	N-Ch	—	8.8	18		
		P-Ch	—	14	28		
$t_{d(off)}$	Turn-Off Delay Time	N-Ch	—	13	26		
		P-Ch	—	20	40		
t_f	Fall Time	N-Ch	—	3.0	6.0		
		P-Ch	—	6.9	14		
C_{iss}	Input Capacitance	N-Ch	—	190	—	pF	N-Channel V_{GS} = 0V, V_{DS} = 15V, ƒ = 1.0MHz P-Channel V_{GS} = 0V, V_{DS} = -15V, ƒ = 1.0MHz
		P-Ch	—	190	—		
C_{oss}	Output Capacitance	N-Ch	—	120	—		
		P-Ch	—	110	—		
C_{rss}	Reverse Transfer Capacitance	N-Ch	—	61	—		
		P-Ch	—	54	—		

Source-Drain Ratings and Characteristics

	Parameter		Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	N-Ch	—	—	1.7	A	
		P-Ch	—	—	-1.3		
I_{SM}	Pulsed Source Current (Body Diode) ①	N-Ch	—	—	16		
		P-Ch	—	—	16		
V_{SD}	Diode Forward Voltage	N-Ch	—	0.82	1.2	V	T_J = 25°C, I_S = 1.25A, V_{GS} = 0V ③
		P-Ch	—	-0.82	-1.2		T_J = 25°C, I_S = -1.25A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	N-Ch	—	27	53	ns	N-Channel T_J = 25°C, I_F =1.25A, di/dt = 100A/µs P-Channel ④ T_J = 25°C, I_F = -1.25A, di/dt = 100A/µs
		P-Ch	—	27	54		
Q_{rr}	Reverse Recovery Charge	N-Ch	—	28	57	nC	
		P-Ch	—	31	62		

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 23)

② N-Channel $I_{SD} \le$ 2.0A, di/dt $\le$ 100A/µs, $V_{DD} \le V_{(BR)DSS}$, $T_J \le$ 150°C
P-Channel $I_{SD} \le$ -1.3A, di/dt $\le$ 84A/µs, $V_{DD} \le V_{(BR)DSS}$, $T_J \le$ 150°C

③ N-Channel Starting T_J = 25°C, L = 22mH R_G = 25Ω, I_{AS} = 2.0A. (See Figure 12)
P-Channel Starting T_J = 25°C, L = 67mH R_G = 25Ω, I_{AS} = -1.3A.

④ Pulse width $\le$ 300µs; duty cycle $\le$ 2%.

⑤ Surface mounted on FR-4 board, t $\le$ 10sec.

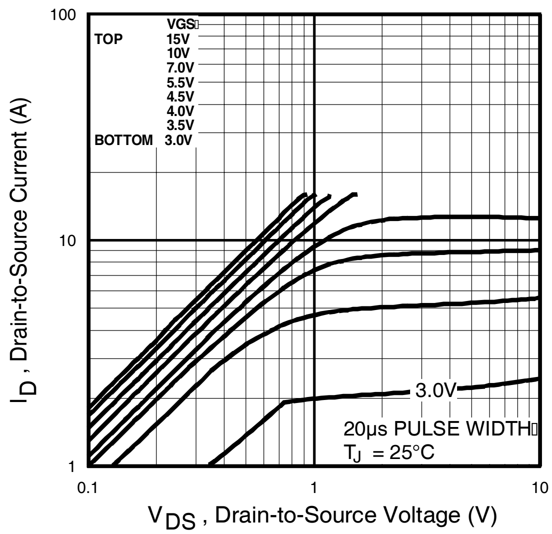


Fig 1. Typical Output Characteristics

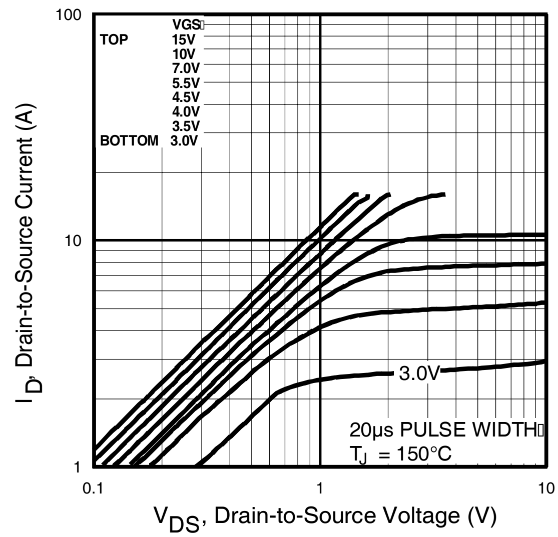


Fig 2. Typical Output Characteristics

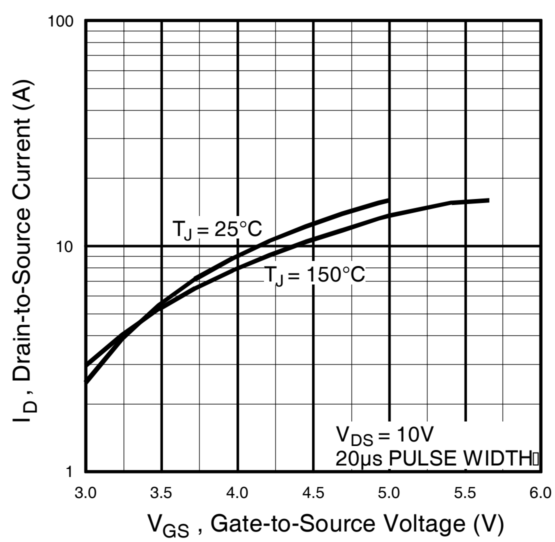


Fig 3. Typical Transfer Characteristics

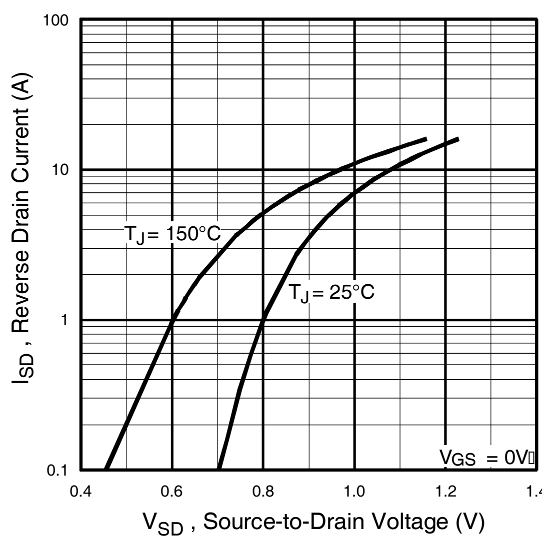


Fig 4. Typical Source-Drain Diode Forward Voltage

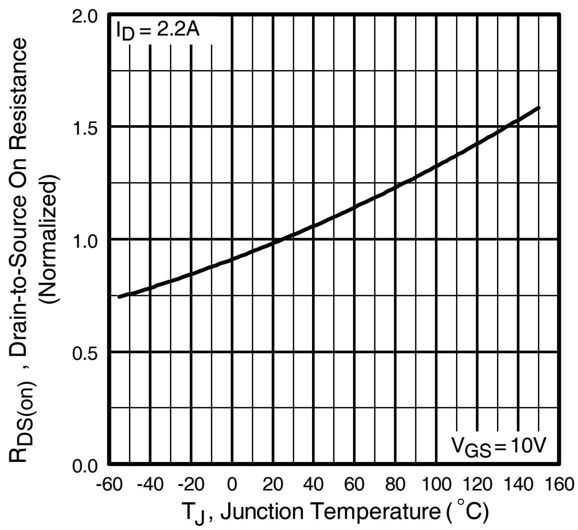


Fig 5. Normalized On-Resistance Vs. Temperature

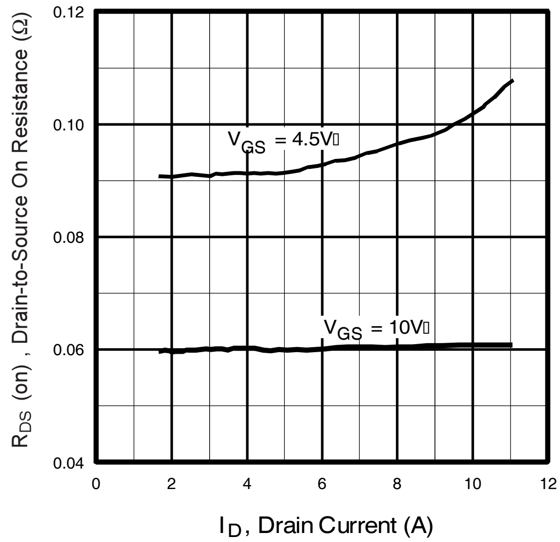


Fig 6. Typical On-Resistance Vs. Drain Current

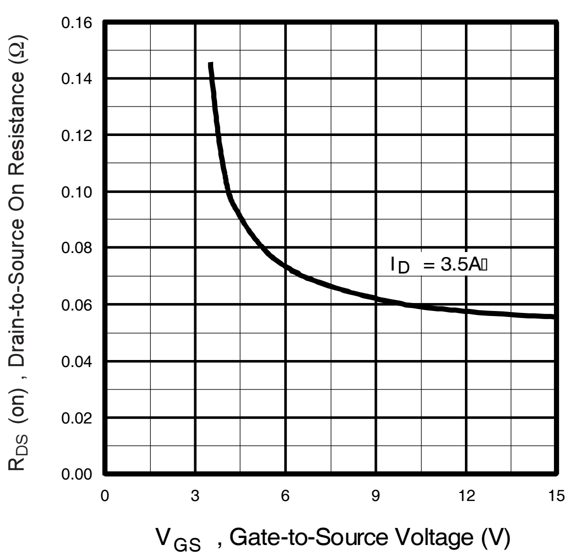


Fig 7. Typical On-Resistance Vs. Gate Voltage

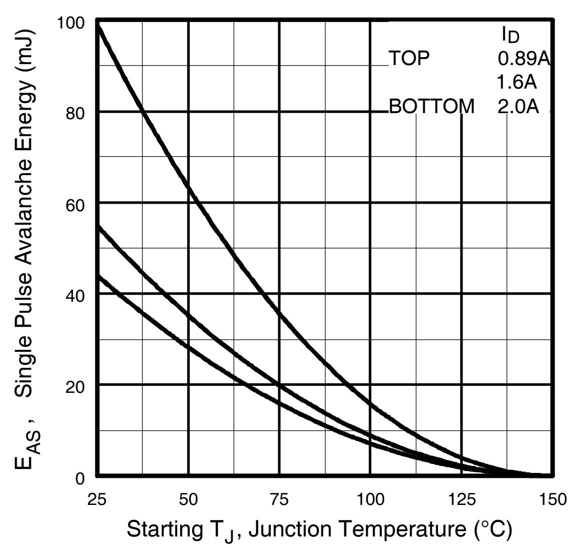


Fig 8. Maximum Avalanche Energy Vs. Drain Current

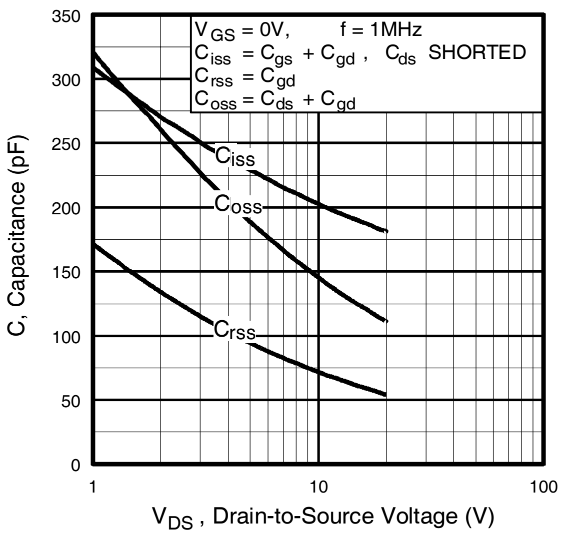


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

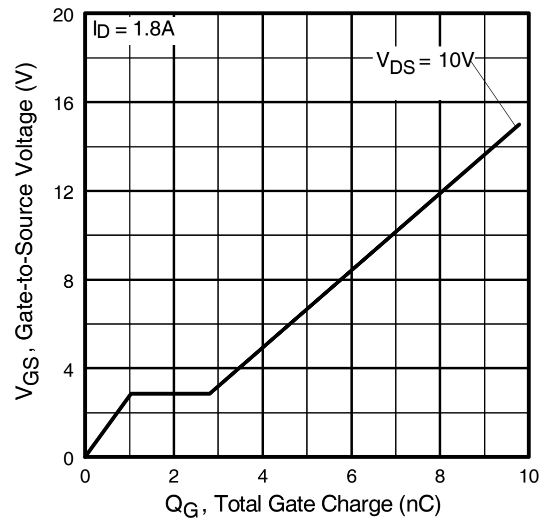


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

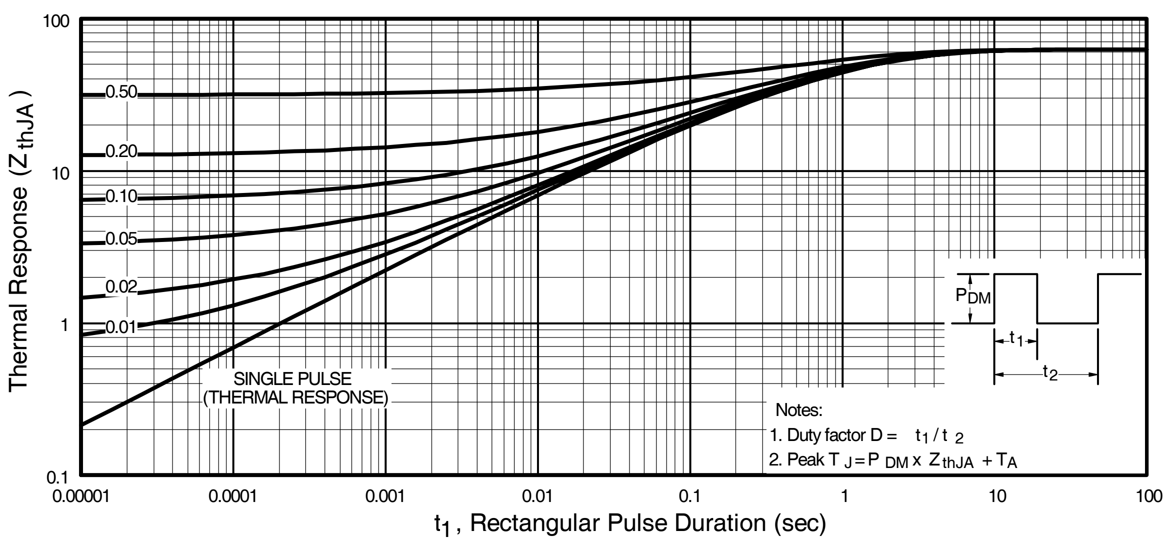


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

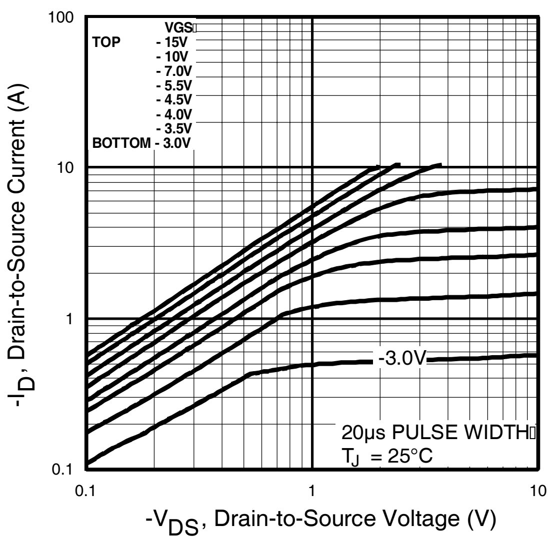


Fig 12. Typical Output Characteristics

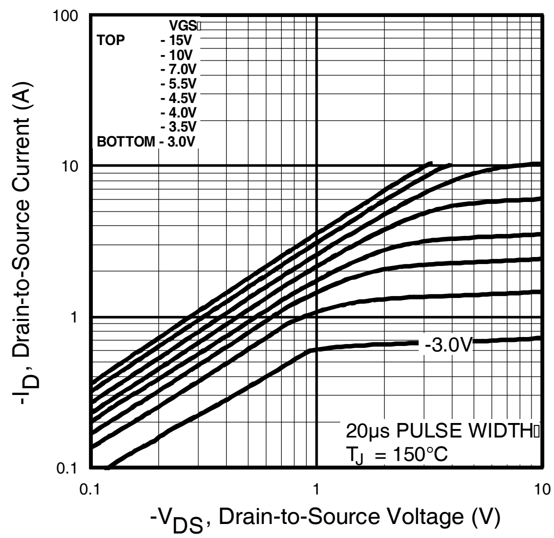


Fig 13. Typical Output Characteristics

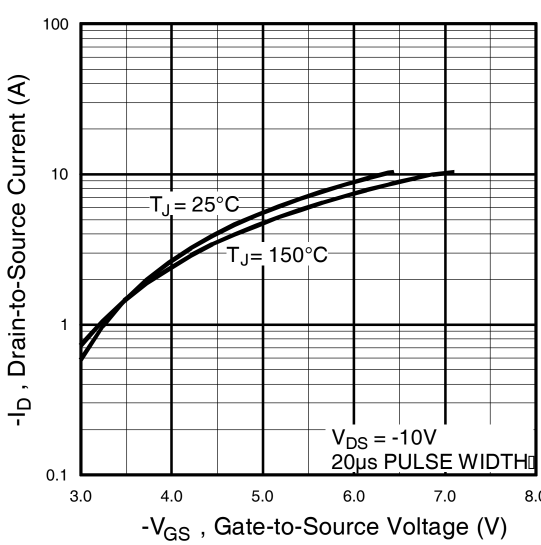


Fig 14. Typical Transfer Characteristics

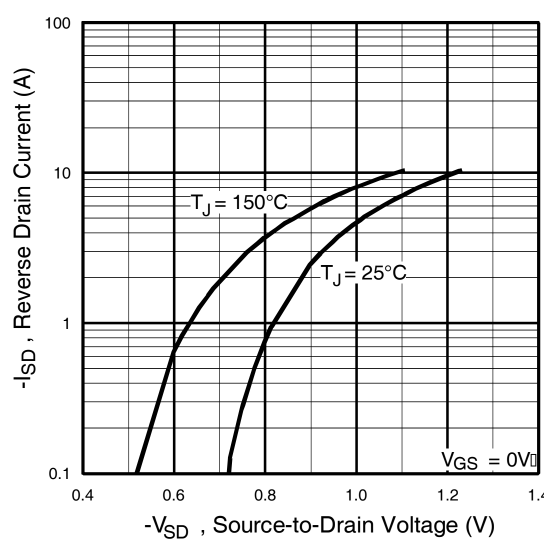


Fig 15. Typical Source-Drain Diode Forward Voltage

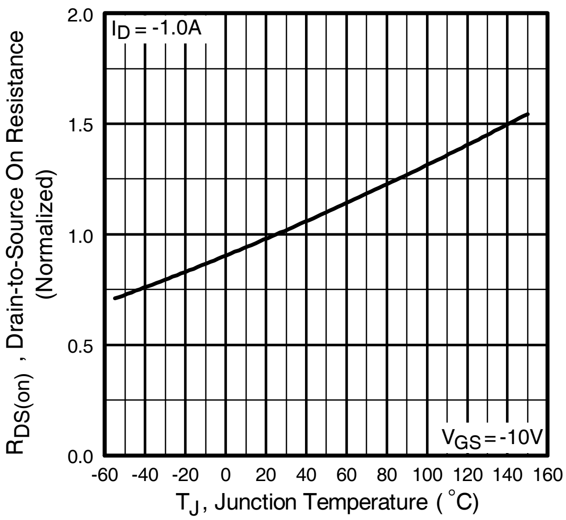


Fig 16. Normalized On-Resistance Vs. Temperature

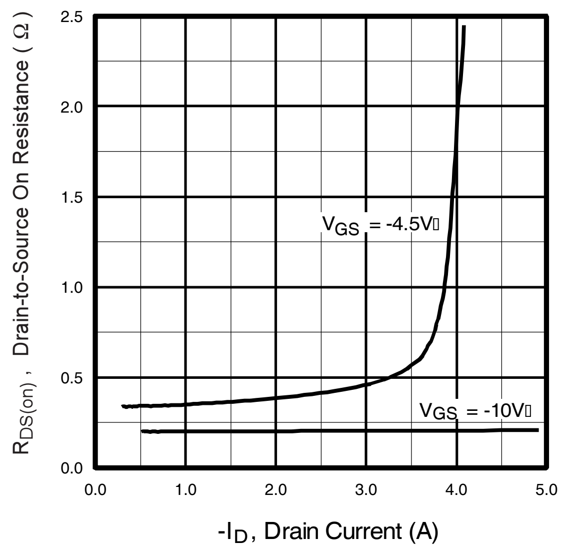


Fig 17. Typical On-Resistance Vs. Drain Current

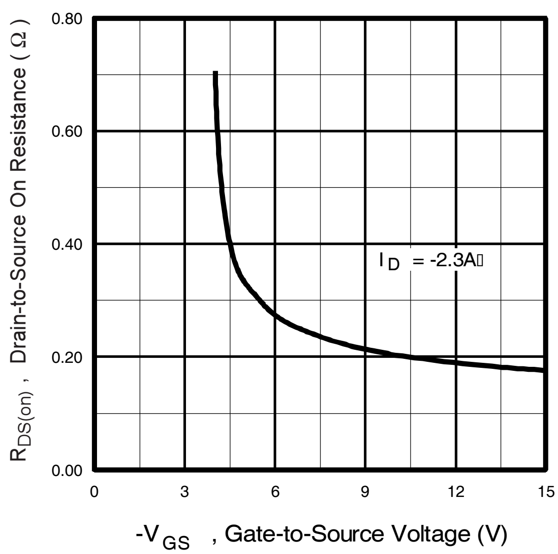


Fig 18. Typical On-Resistance Vs. Gate Voltage

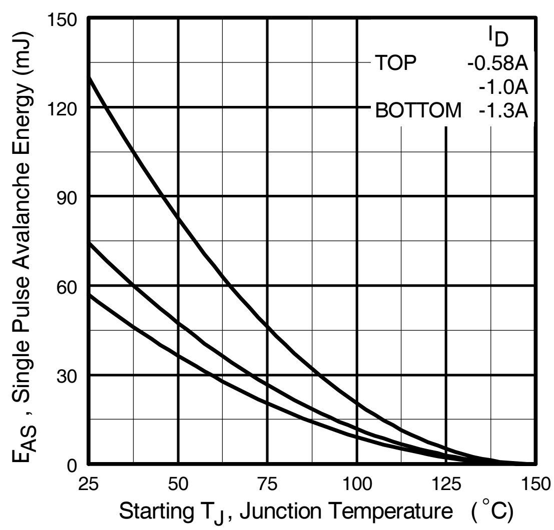


Fig 19. Maximum Avalanche Energy Vs. Drain Current

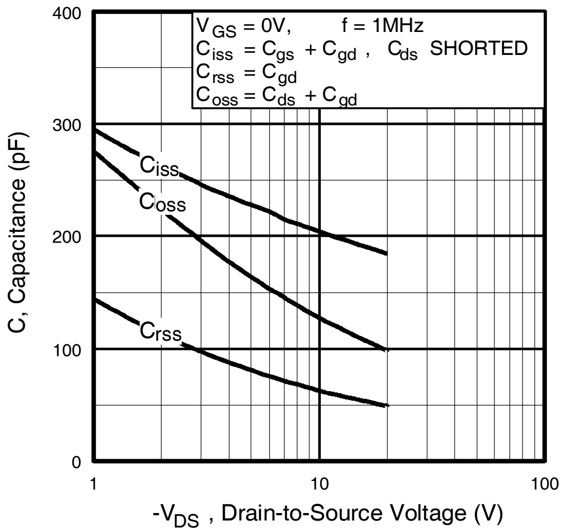


Fig 20. Typical Capacitance Vs. Drain-to-Source Voltage

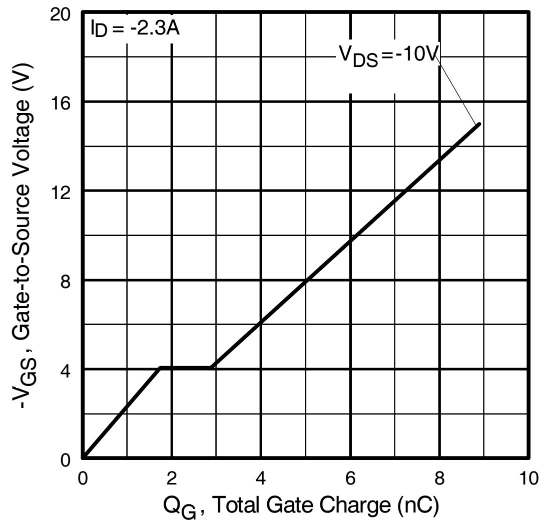


Fig 21. Typical Gate Charge Vs. Gate-to-Source Voltage

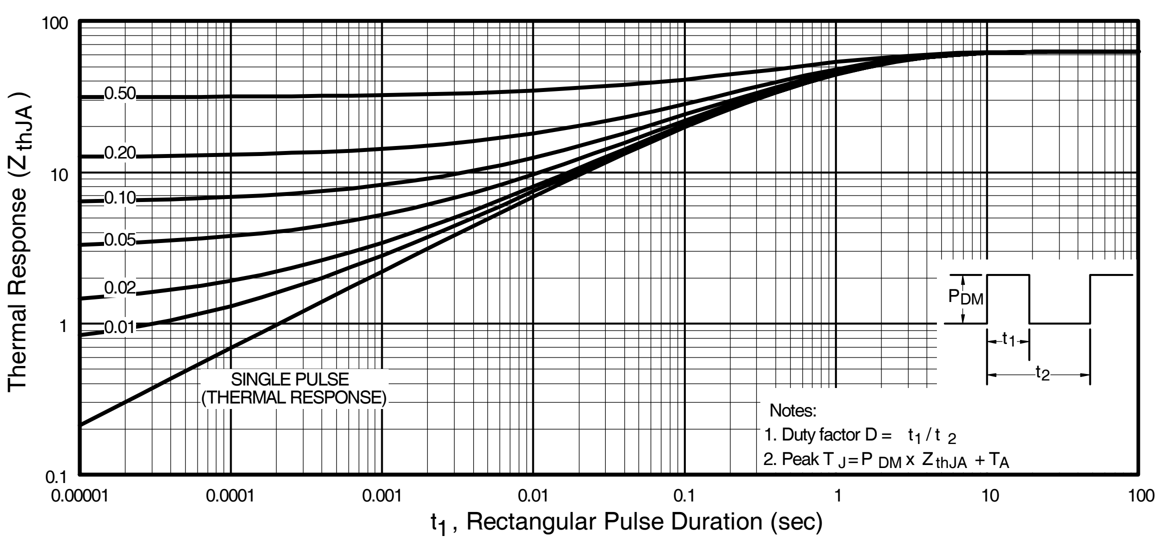
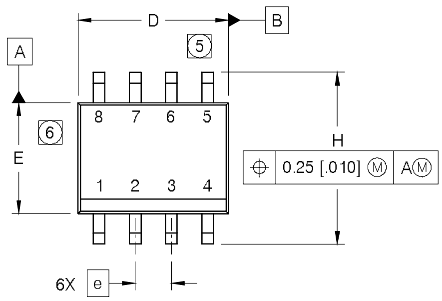


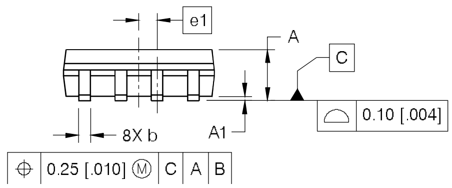
Fig 22. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

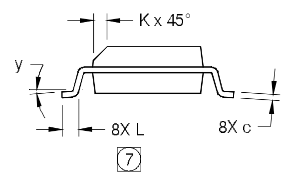
SO-8 Package Outline

Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

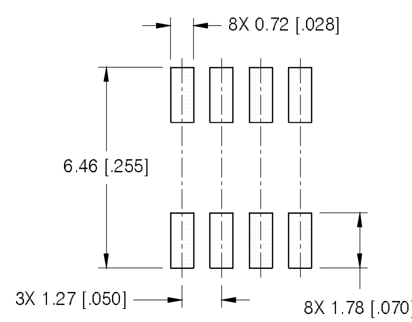




NOTES:

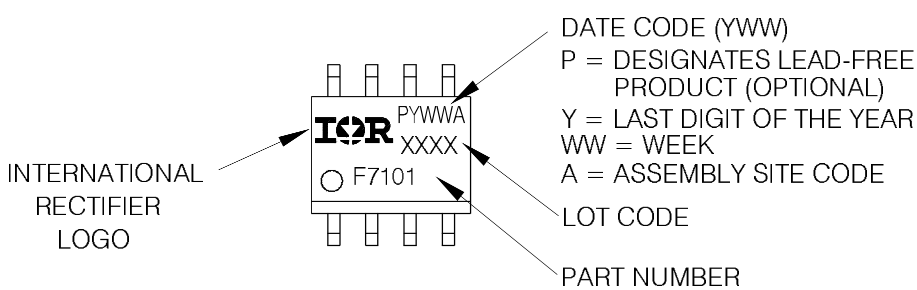
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking

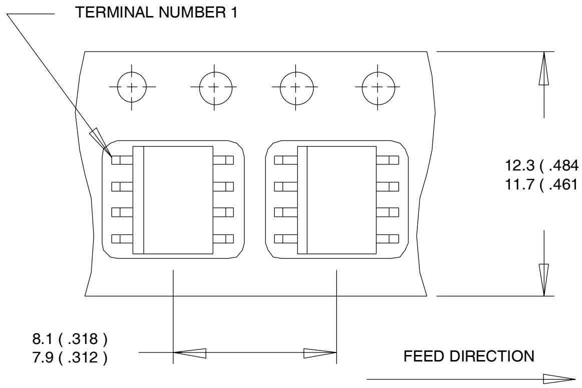
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



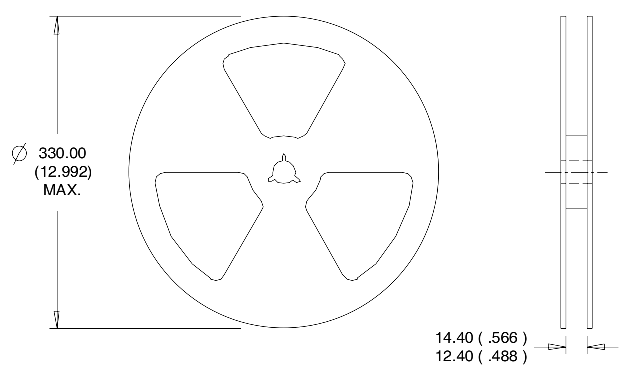
Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Data and specifications subject to change without notice.
This product has been designed and qualified for the Automotive [Q101] market.
Qualification Standards can be found on IR's Web site.

International
IGR Rectifier

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